

STTH60L06TV

Turbo 2 ultrafast high voltage rectifier

Main product characteristics

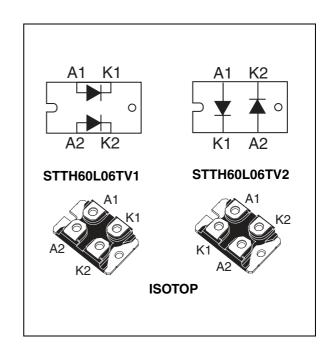
I _{F(AV)}	2 x 40 A
V _{RRM}	600 V
T _j	150° C
V _F (typ)	1.30 V
t _{rr} (typ)	50 ns

Features and benefits

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching & conduction losses
- Insulated package:
 Electrical insulation = 2500 V_{RMS}
 Capacitance = 45 pF

Description

The STTH60L06TV, which is using ST Turbo 2 600V technology, is specially suited for use in switching power supplies, and industrial applications (such as welding), as rectification diode.



Order codes

Part Number	Marking
STTH60L06TV1	STTH60L06TV1
STTH60L06TV2	STTH60L06TV2

Table 1. Absolute ratings (limiting values per diode at 25° C, unless otherwise specified)

Parameter	Value	Unit		
Repetitive peak reverse voltage	600	V		
RMS forward current	100	Α		
Average femueral current S = 0.5	T _c = 75° C per diode	30	Α	
Average forward current, $\delta = 0.5$	T _c = 70° C per diode	40		
Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$		210	Α	
Storage temperature range	-55 to + 150	° C		
Maximum operating junction temperature	150	° C		
	Repetitive peak reverse voltage RMS forward current Average forward current, $\delta = 0.5$ Surge non repetitive forward current Storage temperature range	Repetitive peak reverse voltage	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	

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Table 2. Thermal parameters

Symbol	Parameter		Value	Unit
D	lunation to acco	Per diode	1.60	
R _{th(j-c)} Junction to case	Total	0.85	°C/W	
R _{th(c)}	Coupling thermal resistance		0.1	

When the diodes are used simultaneously:

 $\Delta T_{j(diode1)} = P_{(diode1)} \times R_{th(j-c)} \text{ (per diode)} + P_{(diode2)} \times R_{th(c)}$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test co	nditions	Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Povorco logizado gurrant	T _j = 25° C	V - V			25	μA
'R`	I _R ⁽¹⁾ Reverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		25	250	μΑ
V _F ⁽²⁾ Forward voltage drop	T _j = 25° C	I _E = 60 A			1.55	V	
	T _j = 150° C			1.0	1.25	'	

- 1. Pulse test: t_p = 5 ms, δ < 2 %
- 2. Pulse test: t_p = 380 μ s, δ < 2 %

To evaluate the conduction losses use the following equation:

 $P = 0.95 \text{ x } I_{F(AV)} + 0.010 I_{F}^{2}_{(RMS)}$

Table 4. Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
t _{rr} Reverse recovery time		$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}$ $I_R = 1 \text{ A}, T_j = 25^{\circ} \text{ C}$			65	ns
		I_F = 1 A, dI_F/dt = 50 A/ μ s, V_R = 30 V, T_j = 25° C		65	90	113
I _{RM}	Reverse recovery current	$I_F = 30 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s},$ $V_R = 400 \text{ V}, T_j = 125^{\circ} \text{ C}$		11.5	16	Α
t _{fr}	Forward recovery time	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$			500	ns
V _{FP}	Forward recovery voltage	$I_F = 30 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \ V_{FR} = 1.1 \text{ x }V_{Fmax}, T_j = 25^{\circ} \text{ C}$		2.5		V

STTH60L06TV Characteristics

Figure 1. Conduction losses versus average current (per diode)

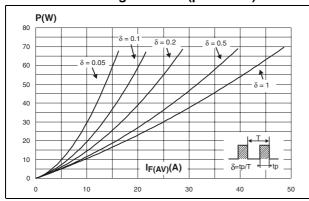


Figure 2. Forward voltage drop versus forward current (per diode)

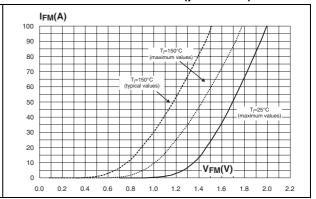


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Zth(j-c)/Rth(j-c)

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

Single pulse

1.E-03

1.E-02

1.E-01

1.E+00

1.E+01

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values, per diode)

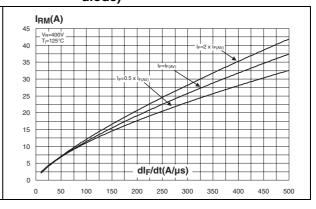


Figure 5. Reverse recovery time versus dl₋/dt (typical values, per diode)

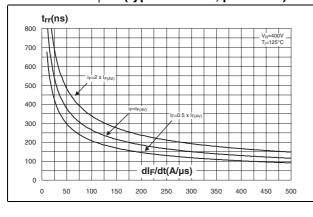
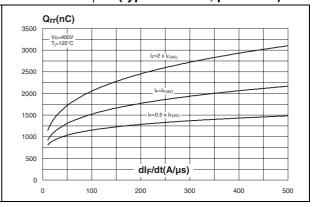


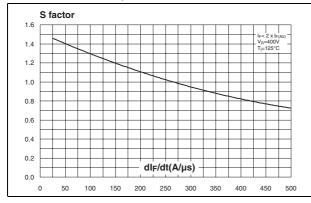
Figure 6. Reverse recovery charges versus dl₋/dt (typical values, per diode)



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Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)

Figure 8. Relative variations of dynamic parameters versus junction temperature



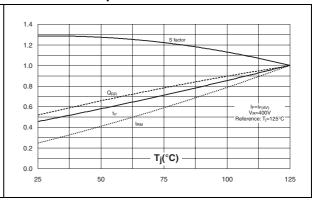
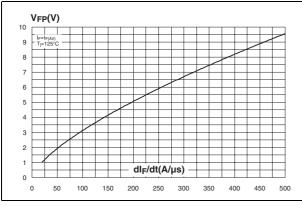


Figure 9. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

Figure 10. Forward recovery time versus dI_F/dt (typical values, per diode)



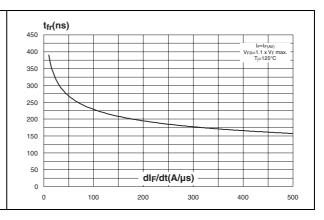
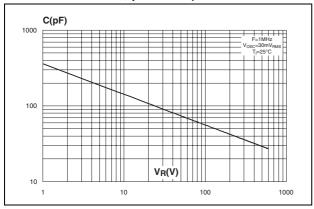


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



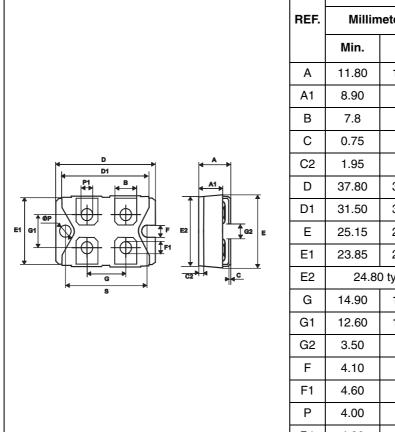
DIMENSIONS

2 Package mechanical data

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 5. ISOTOP dimensions



	DIMENSIONS				
REF.	Millimeters		Inc	hes	
	Min.	Max	Min.	Max.	
Α	11.80	12.20	0.465	0.480	
A1	8.90	9.10	0.350	0.358	
В	7.8	8.20	0.307	0.323	
С	0.75	0.85	0.030	0.033	
C2	1.95	2.05	0.077	0.081	
D	37.80	38.20	1.488	1.504	
D1	31.50	31.70	1.240	1.248	
Е	25.15	25.50	0.990	1.004	
E1	23.85	24.15	0.939	0.951	
E2	24.80 typ.		0.976 typ.		
G	14.90	15.10	0.587	0.594	
G1	12.60	12.80	0.496	0.504	
G2	3.50	4.30	0.138	0.169	
F	4.10	4.30	0.161	0.169	
F1	4.60	5.00	0.181	0.197	
Р	4.00	4.30	0.157	0.69	
P1	4.00	4.40	0.157	0.173	
S	30.10	30.30	1.185	1.193	
•				-	

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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Ordering information STTH60L06TV

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH60L06TV1	STTH60L06TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube
STTH60L06TV2	STTH60L06TV2	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Date	Revision	Description of Changes
07-Sep-2004	1	First issue
10-Sep-2004	2	Average forward current (page 1) and Junction to case (page 2) values changed
13-Oct-2006	3	Reformatted to current standard. Added part number STTH60L06TV2.

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